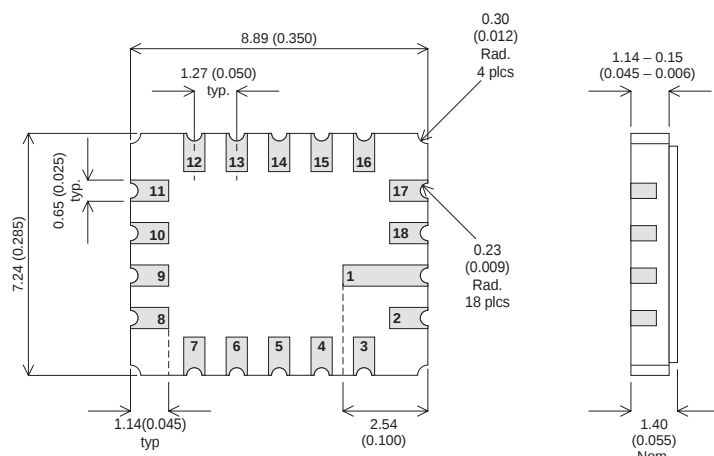


MECHANICAL DATA

Dimensions in mm (inches)



QUAD N-CHANNEL ENHANCEMENT MOSFETS

FEATURES

- HERMETIC CERAMIC SURFACE MOUNT PACKAGE
- LIGHTWEIGHT
- MILITARY SCREENING LEVEL OPTIONS
- SPACE QUALITY LEVELS OPTIONS

APPLICATIONS

- FAST SWITCHING
- MOTOR CONTROLS
- POWER SUPPLIES

LCC18 Ceramic Package

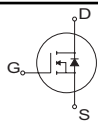
Pin 1 - Drain 1	Pin 2 - N/C	Pin 3 - Gate 1
Pin 4 - Source 1	Pin 5 - Gate 2	Pin 6 - N/C
Pin 7 - Source 2	Pin 8 - N/C	Pin 9 - Drain 2
Pin 10 - Drain 3	Pin 11 - N/C	Pin 12 - Source 3
Pin 13 - Gate 3	Pin 14 - Source 4	Pin 15 - N/C
Pin 16 - Gate 4	Pin 17 - N/C	Pin 18 - Drain 4

ABSOLUTE MAXIMUM RATINGS FOR EACH CHIP ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{DS}	Drain Source Voltage	100V
I_D	Continuous Drain Current	1A
$I_D @ T_c = 100^{\circ}C$	Continuous Drain Current	0.6A
I_{DM}	Pulsed Drain Current *	4A
V_{GS}	Gate Source Voltage	$\pm 20V$
P_D	Maximum Power Dissipation	3.5W
$R_{\theta JC}$	Thermal Resistance Junction to Case	$35.7^{\circ}C/W$
T_J, T_{stg}	Operating and Storage Temperature Range	-55 to $+150^{\circ}C$

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

ELECTRICAL CHARACTERISTICS FOR EACH CHIP ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Parameter		Test Conditions		Min.	Typ.	Max.	Unit
BV _{DSS}	Drain – Source Breakdown Voltage	V _{GS} = 0	I _D = 1mA	100			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS}	I _D = 250μA	2.0		4.0	
I _{GSSF}	Gate – Source Leakage Forward	V _{GS} = 20V				100	nA
I _{GSSR}	Gate – Source Leakage Reverse	V _{GS} = -20V				-100	
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 80V.	V _{GS} =0			25	μA
			T _C = 125°C			250	
R _{DS(on)}	Static Drain Source On-State Resistance*	V _{GS} = 10V	I _D = 0.6A			0.70	Ω
		V _{GS} = 10V	I _D = 1.0A			0.80	
g _{fs}	Forward Transductance *	V _{DS} = 15V	I _{DS} = 0.6A	0.86			S (τ)
C _{iss}	Input Capacitance	V _{GS} = 0	V _{DS} = 25V		180		pF
C _{oss}	Output Capacitance	f = 1MHz			82		
C _{rss}	Reverse Transfer Capacitance				15		
Q _g	Total Gate Charge	V _{GS} = 10V	V _{DS} = 50V			15	nC
Q _{gs}	Gate – Source Charge	I _{DS} = 1.0A				7.5	
Q _{gd}	Gate – Drain Charge					7.5	
t _{d(on)}	Turn–On Delay Time	V _{DD} = 50V	I _D = 1.0A			20	ns
t _r	Rise Time	R _G = 24Ω				25	
t _{d(off)}	Turn–Off Delay Time			(MOSFET switching times are essentially independent of operating temperature.)			
t _f	Fall Time					40	
BODY– DRAIN DIODE RATINGS & CHARACTERISTICS							
I _S	Continuous Source Current Body Diode	Modified MOS POWER symbol showing the intergal 				1.0	A
I _{SM}	Source Current* (Body Diode)	P-N junction rectifier.				4.0	
V _{SD}	Diode Forward Voltage *	I _S = 1.0A	V _{GS} = 0			1.5	V
t _{rr}	Reverse Recovery Time	I _F =1.0A	T _J = 25°C			200	ns
Q _{RR}	Reverse Recovery Charge	d _i / d _t = 100A/μs V _{DD} = 50V				0.83	μC

Notes

* Pulse Test: Pulse Width $\leq 300\mu s$, $\delta \leq 2\%$